

Please check whether you have got the right question paper.

- N.B:**
1. Question No. 1 is compulsory.
 2. Attempt any three questions from remaining five questions.
 3. Assume suitable data where required.
 4. Figures to the right indicate full marks.

Q.1 (solve Any 4)

- a) Compare NMOS & CMOS technology in VLSI design. 05
- b) Implement the following function using Dynamic CMOS logic. 05
- $$Y = \overline{A(B + C)}$$
- c) Compare Ripple carry adder with CLA. 05
- d) Explain working Principle of flash memory. 05
- e) Explain importance of low power design. 05

- Q.2** a) Compare the full scaling & constant voltage scaling models of MOSFETS. Demonstrate the effects of scaling on the area, delay, power consumption and current density of the device 10
- b) Explain transfer characteristics for NMOS. Inverter showing different regions. What is the effect of variation in W/L ratio? 10

- Q.3** a) Draw 1T DRAM cell and explain it's write, read, hold & refresh operation. 10
- b) Explain scheme for multiplication of $101 * 010$. 10

- Q.4** a) Explain various techniques of clock generation & clock distribution. 10
- b) Consider a CMOS Inverter circuit with following parameters. 10

$$V_{DD} = 3.3v.$$

$$V_{To,n} = 0.6v.$$

$$V_{To,p} = -0.7v.$$

$$K_n = 200 \mu A/V^2$$

$$K_p = 80 \mu A/V^2$$

Calculate noise Margins of the circuit Consider $K_R = 2.5$ & $V_{To,n} \neq V_{To,p}$.

- Q.5** a) Draw JK Flip Flop using CMOS and explain the working. 10
- b) Draw CLA (carry lookahead adder) carry chain using dynamic CMOS logic. 10

- Q.6** Write Short notes on (any three) 20

- a) Latch up in CMOS
- b) Sense Amplifier.
- c) Interconnect scaling.
- d) 4*4 Barrel Shifter.